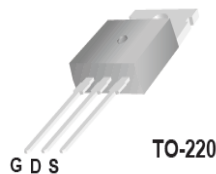


TSP65R700S1

650V 7A N-Channel SJ-MOSFET

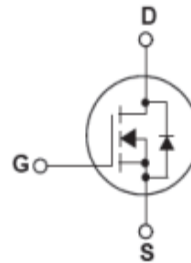
General Description

Truesemi SJ-FET is new generation of high voltage MOSFET family that is utilizing an advanced charge balance mechanism for outstanding low on-resistance and lower gate charge performance. This advanced technology has been tailored to minimize conduction loss, provide superior switching performance, and withstand extreme dv/dt rate and higher avalanche energy. SJ-FET is suitable for various AC/DC power conversion in switching mode operation for higher efficiency.



Features

- 700V @T_J = 150 °C
- Typ. R_{DS(on)} = 0.6Ω
- Ultra Low gate charge (typ. Q_g = 25nC)
- 100% avalanche tested



Absolute Maximum Ratings

Symbol	Parameter	Value	Unit
V _{DSS}	Drain-Source Voltage	650	V
I _D	Drain Current	-Continuous (TC = 25°C)	7
		-Continuous (TC = 100°C)	4.6
I _{DM}	Drain Current – Pulsed (Note 1)	18	A
V _{GSS}	Gate-Source voltage	±30	V
E _{AS}	Single Pulsed Avalanche Energy (Note 2)	86	mJ
I _{AR}	Avalanche Current (Note 1)	1.7	A
E _{AR}	Repetitive Avalanche Energy (Note 1)	0.2	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	15	V/ns
P _D	Power Dissipation (TC = 25°C)	-Derate above 25°C	63
			1.67
T _J , T _{STG}	Operating and Storage Temperature Range	-55 to +150	°C
T _L	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds	300	°C

* Drain current limited by maximum junction temperature.

Thermal Characteristics

Symbol	Parameter	Value	Unit
R _{θJC}	Thermal Resistance, Junction-to-Case	2.0	°C/W
R _{θCS}	Thermal Resistance, Case-to-Sink Typ.	0.5	°C/W
R _{θJA}	Thermal Resistance, Junction-to-Ambient	62	°C/W

Electrical Characteristics TC = 25 °C unless otherwise noted

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A, T_J = 25^\circ C$	650	--	--	V
		$V_{GS} = 0V, I_D = 250\mu A, T_J = 150^\circ C$	--	700	--	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250\mu A$, Referenced to 25 °C	--	0.6	--	V/°C
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 650V, V_{GS} = 0V, -T_J = 150^\circ C$	--	-- 10	1 --	μA μA
I_{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = 30V, V_{DS} = 0V$	--	--	100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = -30V, V_{DS} = 0V$	--	--	-100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu A$	2.5	3.5	4.5	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10V, I_D = 3.5A$	--	0.6	0.7	Ω
g_{FS}	Forward Trans conductance	$V_{DS} = 40V, I_D = 3.5A$ (Note 4)	--	16	--	S
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{DS} = 25V, V_{GS} = 0V, f = 1.0MHz$	--	380	--	pF
C_{oss}	Output Capacitance		--	110	--	pF
C_{rss}	Reverse Transfer Capacitance		--	7	--	pF
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 400V, I_D = 3.5A, R_G = 20\Omega$ (Note 4 , 5)	--	13	--	ns
t_r	Turn-On Rise Time		--	10	--	ns
$t_{d(off)}$	Turn-Off Delay Time		--	85	--	ns
t_f	Turn-Off Fall Time		--	14	--	ns
Q_g	Total Gate Charge	$V_{DS} = 480V, I_D = 3.5A, V_{GS} = 10V$ (Note 4,5)	--	25	--	nC
Q_{gs}	Gate-Source Charge		--	2.0	--	nC
Q_{gd}	Gate-Drain Charge		--	2.7	--	nC
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain-Source Diode Forward Current		--	--	7	A
I_{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	18	A
V_{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0V, I_F = 3.5A$	--	0.9	1.5	V
t_{rr}	Reverse Recovery Time	$V_{GS} = 0V, I_F = 3.5A, di_F/dt = 100A/\mu s$ (Note 4)	--	190	--	ns
Q_{rr}	Reverse Recovery Charge		--	2.3	--	μC

NOTES:

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. L=60mH, $I_{AS}=1.7A, V_{DD}=50V$, Starting $T_J=25^\circ C$
3. $I_{SD} \leq 7A, di/dt \leq 200A/\mu s, V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ C$
4. Pulse Test: Pulse width $\leq 300\mu s$, Duty Cycle $\leq 2\%$
5. Essentially Independent of Operating Temperature Typical Characteristics

Typical Performance Characteristics

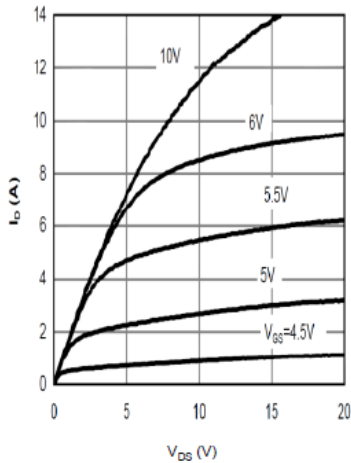


Figure 1: On-Region Characteristics@25°C

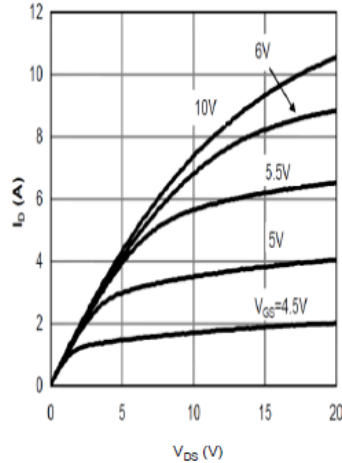


Figure 2: On-Region Characteristics@125°C

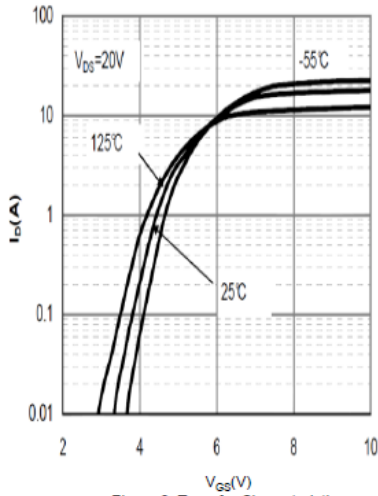


Figure 3: Transfer Characteristics

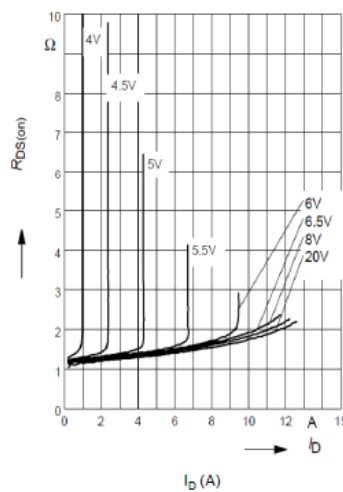


Figure 4: On-Resistance vs. Drain Current and Gate Voltage

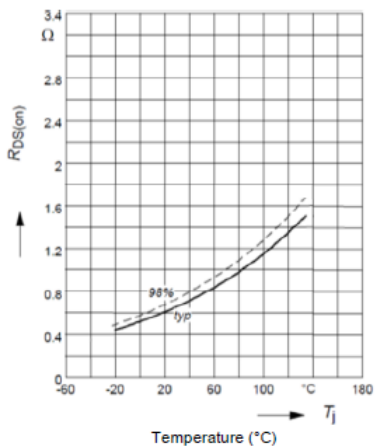


Figure 5: On-Resistance vs. Junction Temperature

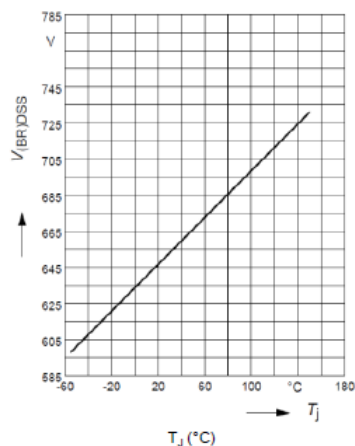


Figure 6: Break Down vs. Junction Temperature

Typical Performance Characteristics

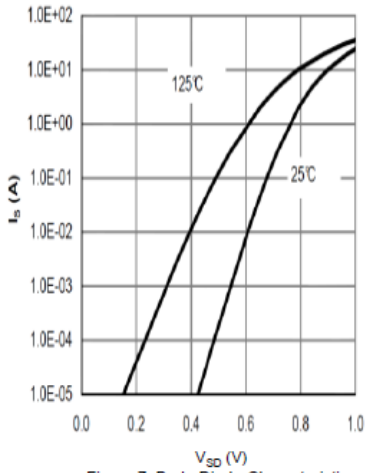


Figure 7: Body-Diode Characteristics

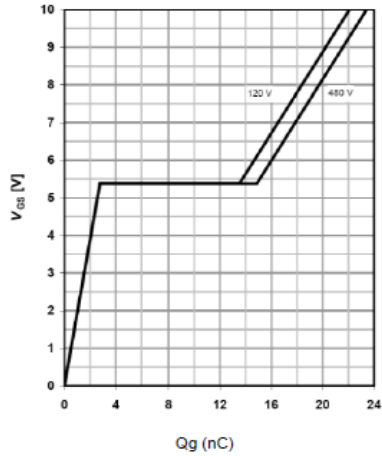


Figure 8: Gate-Charge Characteristics

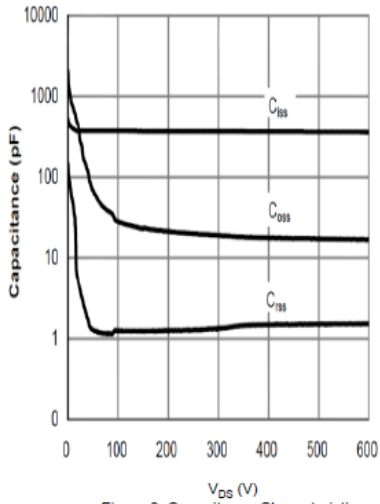


Figure 9: Capacitance Characteristics

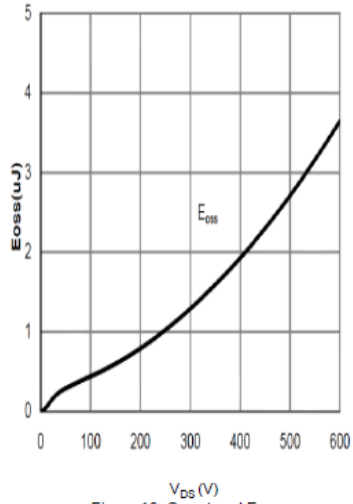


Figure 10: C_{oss} stored Energy

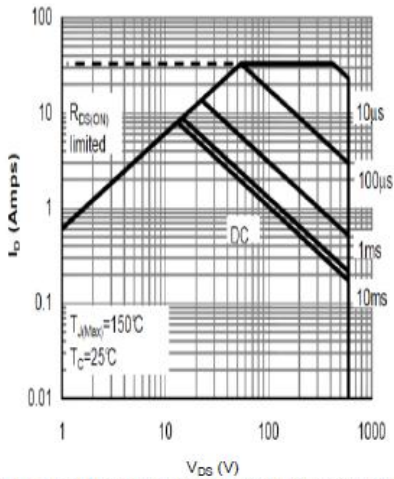


Figure 11: Maximum Forward Biased Safe Operating Area

Typical Performance Characteristics

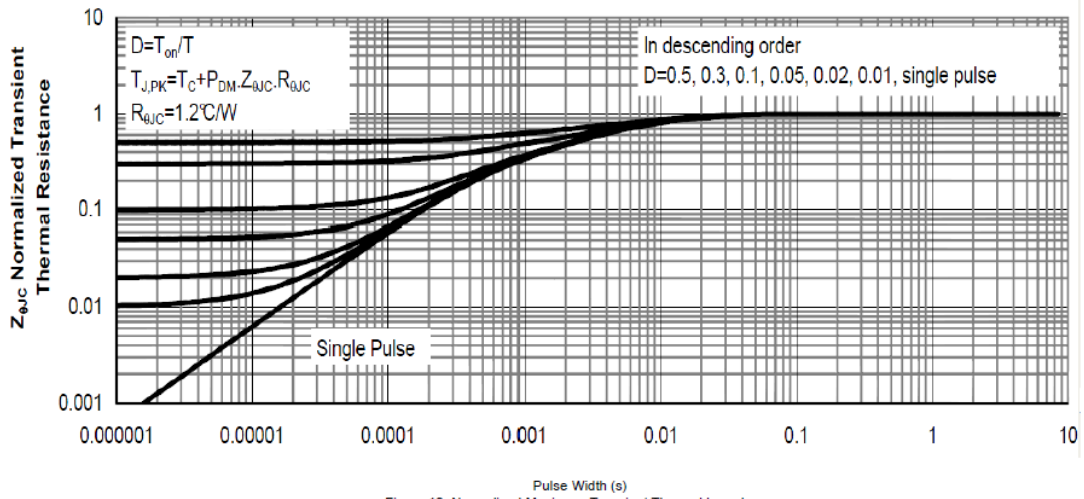


Figure 12: Normalized Maximum Transient Thermal Impedance

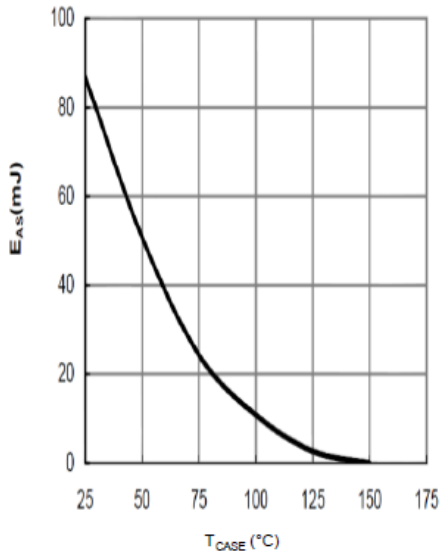


Figure 13: Avalanche energy

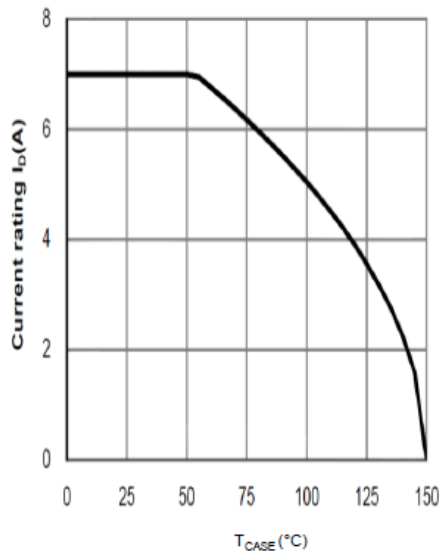


Figure 14: Current De-rating

Typical Performance Characteristics

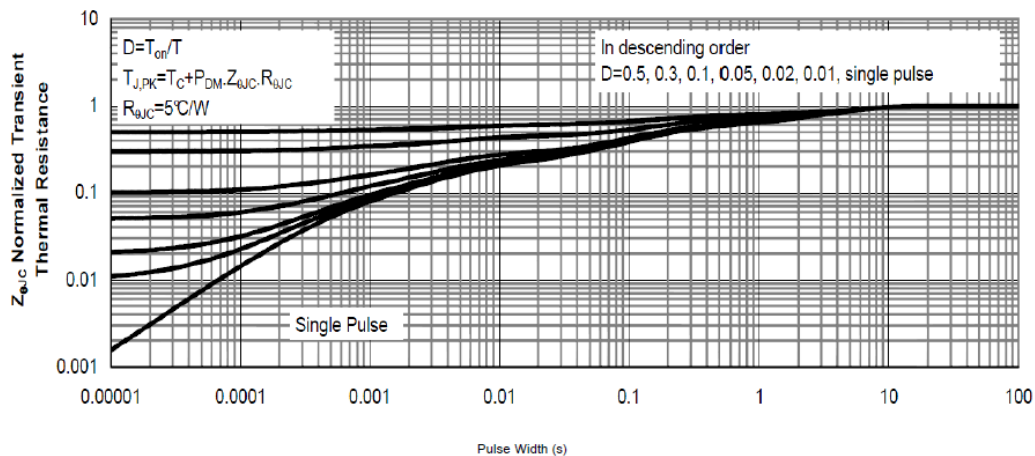
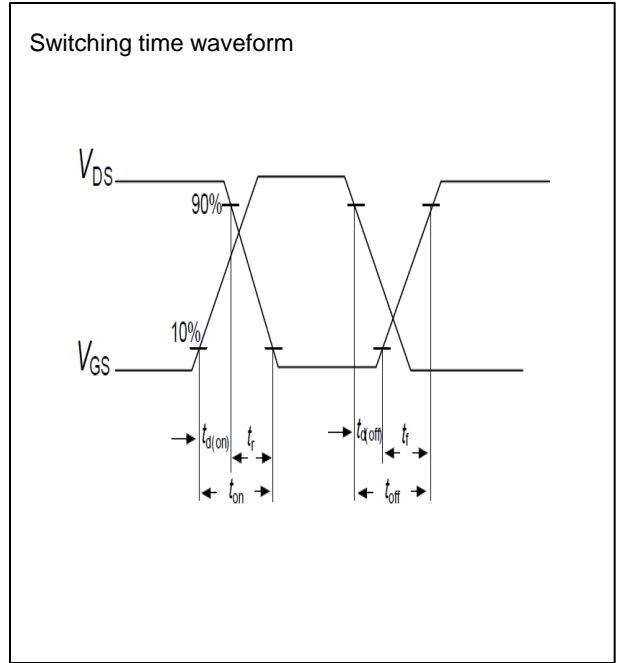
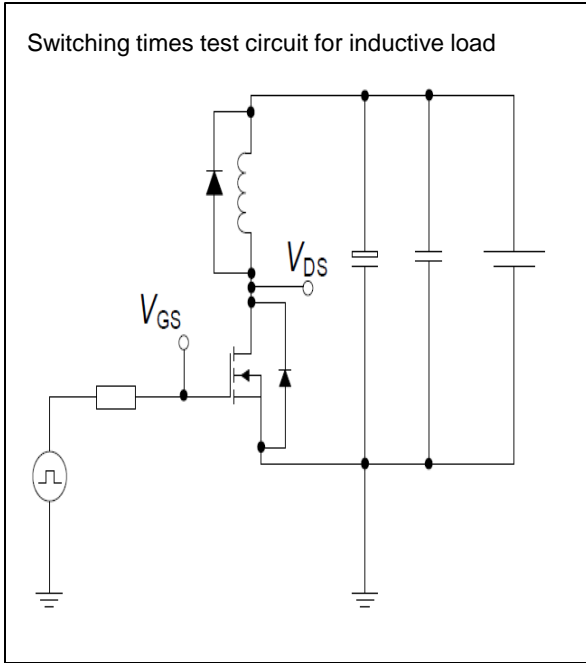


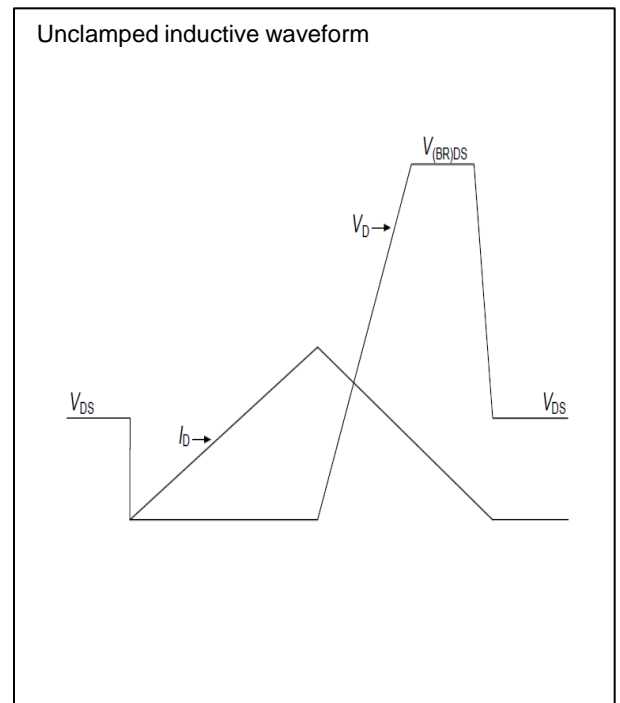
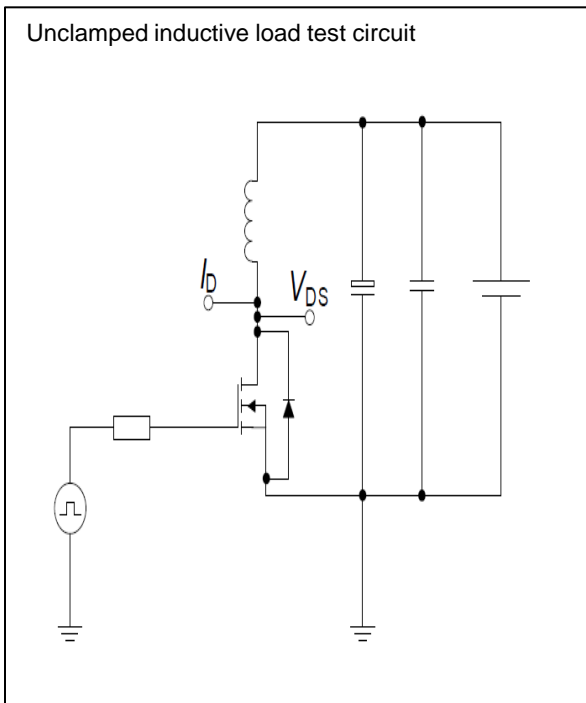
Figure 15: Normalized Maximum Transient Thermal Impedance

Test circuits

Switching times test circuit and waveform for inductive load

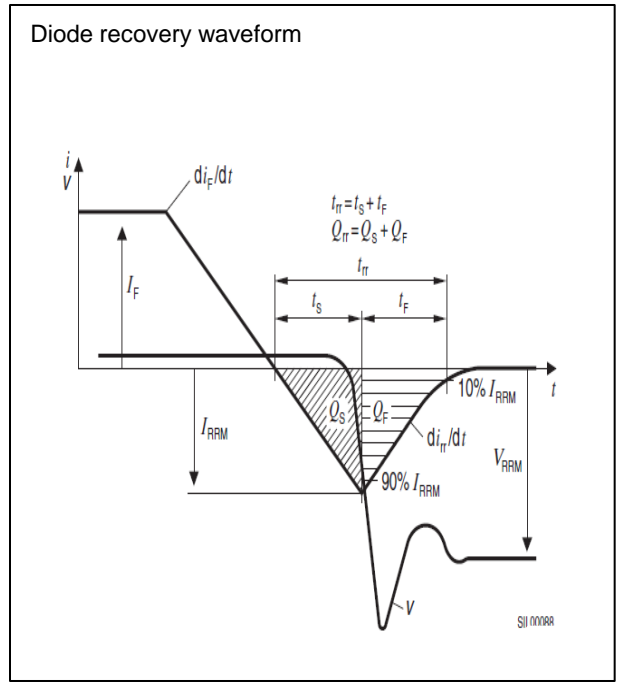
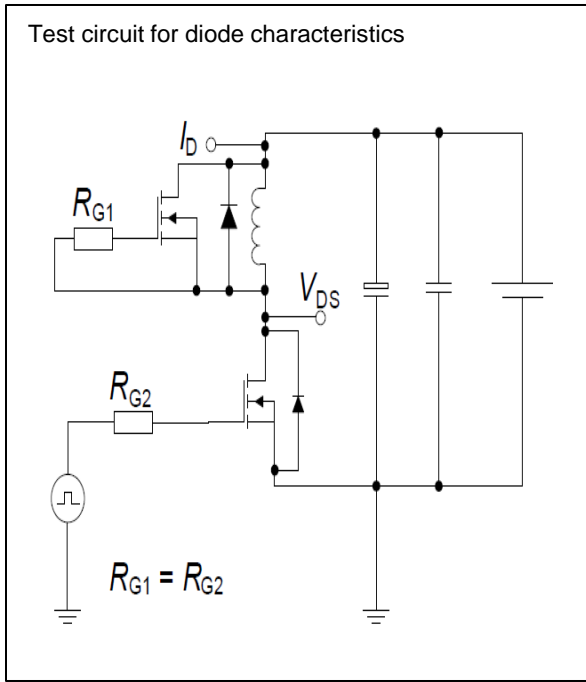


Unclamped inductive load test circuit and waveform



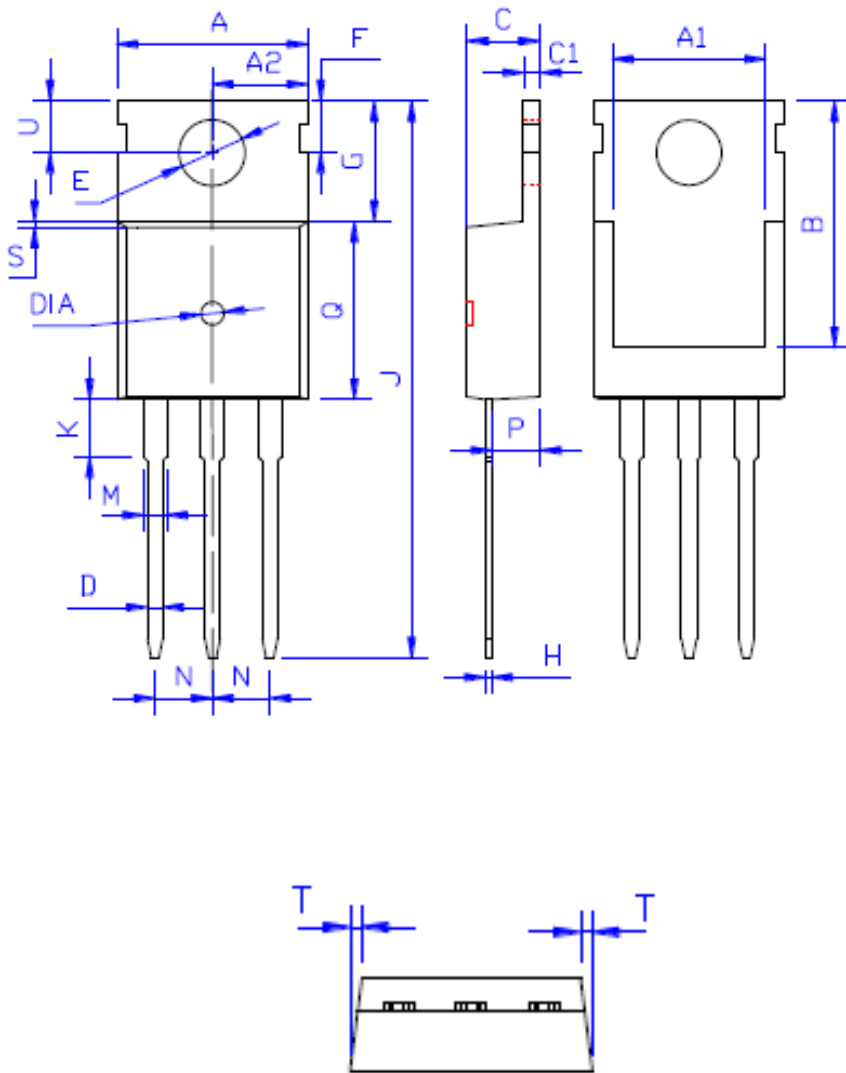
Test circuits

Test circuit and waveform for diode characteristics



Package Outline TO-220

TSP65R700S1 650V 7A N-Channel SJ-MOSFET



DIM	MILLIMETERS
A	10.00 ± 0.30
A1	8.00 ± 0.30
A2	5.00 ± 0.30
B	13.20 ± 0.40
C	4.50 ± 0.20
C1	1.30 ± 0.20
D	0.80 ± 0.20
E	3.60 ± 0.20
F	3.00 ± 0.30
G	6.60 ± 0.40
H	0.50 ± 0.20
J	28.88 ± 0.50
K	3.00 ± 0.30
M	1.30 ± 0.30
N	Typical 2.54
P	2.40 ± 0.40
Q	9.20 ± 0.40
S	0.25 ± 0.15
T	0.25 ± 0.15
U	2.80 ± 0.30
DIA	宽 1.50 ± 0.10 深 0.50 MAX